

### FEATURES

- Bidirectional logic level translation
- Operates from 1.15 V to 5.5 V
- Low quiescent current < 1  $\mu$ A
- No direction pin

### APPLICATIONS

- Low voltage ASIC level translation
- Smart card readers
- Cell phones and cell phone cradles
- Portable communication devices
- Telecommunications equipment
- Network switches and routers
- Storage systems (SAN/NAS)
- Computing/server applications
- GPS
- Portable POS systems
- Low cost serial interfaces

### FUNCTIONAL BLOCK DIAGRAM

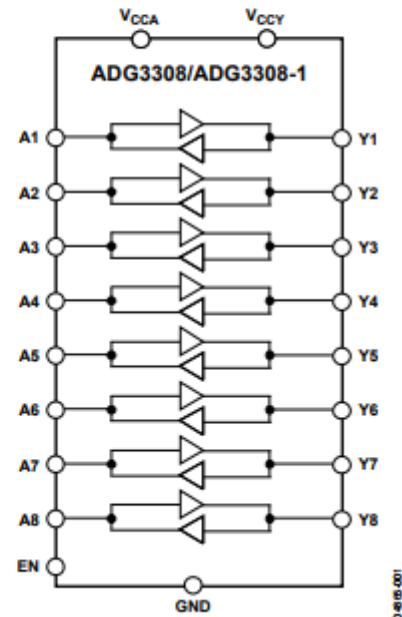


Figure 1.

### GENERAL DESCRIPTION

The **ADG3308/ADG3308-1** are bidirectional level translators containing eight bidirectional channels. They can be used in multivoltage digital system applications, such as a data transfer between a low voltage DSP controller and a higher voltage device. The internal architecture allows the device to perform bidirectional level translation without an additional signal to set the direction in which the translation takes place.

The voltage applied to  $V_{CCA}$  sets the logic levels on the A side of the device, and  $V_{CCY}$  sets the levels on the Y side. For proper operation,  $V_{CCA}$  must always be less than  $V_{CCY}$ . The  $V_{CCA}$  compatible logic signals applied to the A side of the device appear as  $V_{CCY}$  compatible levels on the Y side. Similarly,  $V_{CCY}$  compatible logic levels applied to the Y side of the device appear as  $V_{CCA}$  compatible logic levels on the A side.

The enable pin (EN) provides three-state operation on both the A side and the Y side pins. When the EN pin is pulled low, the terminals on both sides of the device are in the high impedance state. For normal operation, EN should be driven high.

The **ADG3308** is available in a compact 20-lead TSSOP and a 20-lead LFCSP. The **ADG3308-1** is available in a 20-ball WLCSP. The EN pin is referred to the  $V_{CCY}$  supply voltage for the **ADG3308** and to the  $V_{CCA}$  supply voltage for the **ADG3308-1**.

The **ADG3308/ADG3308-1** are guaranteed to operate over the 1.15 V to 5.5 V supply voltage range and the extended  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$  temperature range.

### PRODUCT HIGHLIGHTS

1. Bidirectional logic level translation.
2. Fully guaranteed over the 1.15 V to 5.5 V supply range.
3. No direction pin.
4. Packages: 20-lead TSSOP and 20-lead LFCSP (**ADG3308**) and 20-ball WLCSP (**ADG3308-1**).

# SPECIFICATIONS

$V_{CCY} = 1.65\text{ V to }5.5\text{ V}$ ,  $V_{CCA} = 1.15\text{ V to }V_{CCY}$ ,  $GND = 0\text{ V}$ . All specifications  $T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted.<sup>1</sup>

Table 1.

Parameter	Symbol	Conditions	Min	Typ <sup>2</sup>	Max	Unit
<b>LOGIC INPUTS/OUTPUTS</b>						
<b>A Side</b>						
Input High Voltage <sup>3</sup>	$V_{IHA}$	$V_{CCA} = 1.15\text{ V}$	$V_{CCA} - 0.3$			V
	$V_{IHA}$	$V_{CCA} = 1.2\text{ V to }5.5\text{ V}$	$0.65 \times V_{CCA}$			V
Input Low Voltage <sup>3</sup>	$V_{ILA}$				$0.35 \times V_{CCA}$	V
Output High Voltage	$V_{OHA}$	$V_Y = V_{CCY}$ , $I_{OH} = 20\ \mu\text{A}$ , see Figure 29	$V_{CCA} - 0.4$			V
Output Low Voltage	$V_{OLA}$	$V_Y = 0\text{ V}$ , $I_{OL} = 20\ \mu\text{A}$ , see Figure 29			0.4	V
Capacitance <sup>3</sup>	$C_A$	$f = 1\text{ MHz}$ , $EN = 0$ , see Figure 34		10		pF
Leakage Current	$I_{LA, HIGH-Z}$	$V_A = 0\text{ V or }V_{CCA}$ , $EN = 0$ , see Figure 31			$\pm 1$	$\mu\text{A}$
<b>Y Side</b>						
Input High Voltage <sup>3</sup>	$V_{IHY}$		$0.65 \times V_{CCY}$			V
Input Low Voltage <sup>3</sup>	$V_{ILY}$				$0.35 \times V_{CCY}$	V
Output High Voltage	$V_{OHY}$	$V_A = V_{CCA}$ , $I_{OH} = 20\ \mu\text{A}$ , see Figure 30	$V_{CCY} - 0.4$			V
Output Low Voltage	$V_{OLY}$	$V_A = 0\text{ V}$ , $I_{OL} = 20\ \mu\text{A}$ , see Figure 30			0.4	V
Capacitance <sup>3</sup>	$C_Y$	$f = 1\text{ MHz}$ , $EN = 0$ , see Figure 35		6.8		pF
Leakage Current	$I_{LY, HIGH-Z}$	$V_Y = 0\text{ V or }V_{CCY}$ , $EN = 0$ , see Figure 32			$\pm 1$	$\mu\text{A}$
<b>Enable (EN)</b>						
Input High Voltage <sup>3</sup>	$V_{IHEN}$		$0.65 \times V_{CCY}$			V
ADG3308 (TSSOP, LFCSP)		$V_{CCA} = 1.15\text{ V}$	$V_{CCA} - 0.3$			V
ADG3308-1 (WLCSP)		$V_{CCA} = 1.2\text{ V to }5.5\text{ V}$	$0.65 \times V_{CCA}$			V
Input Low Voltage <sup>3</sup>	$V_{ILEN}$				$0.35 \times V_{CCY}$	V
ADG3308 (TSSOP, LFCSP)					$0.35 \times V_{CCA}$	V
ADG3308-1 (WLCSP)					$\pm 1$	$\mu\text{A}$
Leakage Current	$I_{LEN}$	$V_{BN} = 0\text{ V or }V_{CCY}$ , $V_A = 0\text{ V}$ , see Figure 33			$\pm 1$	$\mu\text{A}$
Capacitance <sup>3</sup>	$C_{EN}$			4.5		pF
Enable Time <sup>3</sup>	$t_{EN}$	$R_S = R_T = 50\ \Omega$ , $V_A = 0\text{ V or }V_{CCA}$ (A $\rightarrow$ Y), $V_Y = 0\text{ V or }V_{CCY}$ (Y $\rightarrow$ A), see Figure 36		1	1.8	$\mu\text{s}$
<b>SWITCHING CHARACTERISTICS<sup>3</sup></b>						
$3.3\text{ V} \pm 0.3\text{ V} \leq V_{CCA} \leq V_{CCY}$ , $V_{CCY} = 5\text{ V} \pm 0.5\text{ V}$						
<b>A<math>\rightarrow</math>Y Level Translation</b>						
$R_S = R_T = 50\ \Omega$ , $C_L = 50\text{ pF}$ , see Figure 37						
Propagation Delay	$t_{P, A\rightarrow Y}$			6	10	ns
Rise Time	$t_{R, A\rightarrow Y}$			2	3.5	ns
Fall Time	$t_{F, A\rightarrow Y}$			2	3.5	ns
Maximum Data Rate	$D_{MAX, A\rightarrow Y}$		50			Mbps
Channel-to-Channel Skew	$t_{SKEW, A\rightarrow Y}$			2	4	ns
Part-to-Part Skew	$t_{PPSKEW, A\rightarrow Y}$				3	ns
<b>Y<math>\rightarrow</math>A Level Translation</b>						
$R_S = R_T = 50\ \Omega$ , $C_L = 15\text{ pF}$ , see Figure 38						
Propagation Delay	$t_{P, Y\rightarrow A}$			4	7	ns
Rise Time	$t_{R, Y\rightarrow A}$			1	3	ns
Fall Time	$t_{F, Y\rightarrow A}$			3	7	ns
Maximum Data Rate	$D_{MAX, Y\rightarrow A}$		50			Mbps
Channel-to-Channel Skew	$t_{SKEW, Y\rightarrow A}$			2	3.5	ns
Part-to-Part Skew	$t_{PPSKEW, Y\rightarrow A}$				2	ns

Parameter	Symbol	Conditions	Min	Typ <sup>2</sup>	Max	Unit			
<b>1.8 V ± 0.15 V ≤ V<sub>CCA</sub> ≤ V<sub>CCY</sub>, V<sub>CCY</sub> = 3.3 V ± 0.3 V</b>									
A→Y Level Translation		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 50 pF, see Figure 37	50						
Propagation Delay	t <sub>P, A→Y</sub>						8	11	ns
Rise Time	t <sub>R, A→Y</sub>						2	5	ns
Fall Time	t <sub>F, A→Y</sub>						2	5	ns
Maximum Data Rate	D <sub>MAX, A→Y</sub>								Mbps
Channel-to-Channel Skew	t <sub>SKEW, A→Y</sub>						2	4	ns
Part-to-Part Skew	t <sub>PPSKEW, A→Y</sub>		4	ns					
Y→A Level Translation		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 15 pF, see Figure 38	50						
Propagation Delay	t <sub>P, Y→A</sub>						5	8	ns
Rise Time	t <sub>R, Y→A</sub>						2	3.5	ns
Fall Time	t <sub>F, Y→A</sub>						2	3.5	ns
Maximum Data Rate	D <sub>MAX, Y→A</sub>								Mbps
Channel-to-Channel Skew	t <sub>SKEW, Y→A</sub>						2	3	ns
Part-to-Part Skew	t <sub>PPSKEW, Y→A</sub>		3	ns					
<b>1.15 V to 1.3 V ≤ V<sub>CCA</sub> ≤ V<sub>CCY</sub>, V<sub>CCY</sub> = 3.3 V ± 0.3 V</b>									
A→Y Level Translation		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 50 pF, see Figure 37	40						
Propagation Delay	t <sub>P, A→Y</sub>						9	18	ns
Rise Time	t <sub>R, A→Y</sub>						3	5	ns
Fall Time	t <sub>F, A→Y</sub>						2	5	ns
Maximum Data Rate	D <sub>MAX, A→Y</sub>								Mbps
Channel-to-Channel Skew	t <sub>SKEW, A→Y</sub>						2	5	ns
Part-to-Part Skew	t <sub>PPSKEW, A→Y</sub>		10	ns					
Y→A Level Translation		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 15 pF, see Figure 38	40						
Propagation Delay	t <sub>P, Y→A</sub>						5	9	ns
Rise Time	t <sub>R, Y→A</sub>						2	4	ns
Fall Time	t <sub>F, Y→A</sub>						2	4	ns
Maximum Data Rate	D <sub>MAX, Y→A</sub>								Mbps
Channel-to-Channel Skew	t <sub>SKEW, Y→A</sub>						2	4	ns
Part-to-Part Skew	t <sub>PPSKEW, Y→A</sub>		4	ns					
<b>1.15 V to 1.3 V ≤ V<sub>CCA</sub> ≤ V<sub>CCY</sub>, V<sub>CCY</sub> = 1.8 V ± 0.3 V</b>									
A→Y Level Translation		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 50 pF, see Figure 37	25						
Propagation Delay	t <sub>P, A→Y</sub>						12	25	ns
Rise Time	t <sub>R, A→Y</sub>						7	12	ns
Fall Time	t <sub>F, A→Y</sub>						3	5	ns
Maximum Data Rate	D <sub>MAX, A→Y</sub>								Mbps
Channel-to-Channel Skew	t <sub>SKEW, A→Y</sub>						2	5	ns
Part-to-Part Skew	t <sub>PPSKEW, A→Y</sub>		15	ns					
Y→A Level Translation		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 15 pF, see Figure 38	25						
Propagation Delay	t <sub>P, Y→A</sub>						14	35	ns
Rise Time	t <sub>R, Y→A</sub>						5	16	ns
Fall Time	t <sub>F, Y→A</sub>						2.5	6.5	ns
Maximum Data Rate	D <sub>MAX, Y→A</sub>								Mbps
Channel-to-Channel Skew	t <sub>SKEW, Y→A</sub>						3	6.5	ns
Part-to-Part Skew	t <sub>PPSKEW, Y→A</sub>		23.5	ns					

Parameter	Symbol	Conditions	Min	Typ <sup>2</sup>	Max	Unit
2.5 V ± 0.2 V ≤ V <sub>CCA</sub> ≤ V <sub>CCY</sub> , V <sub>CCY</sub> = 3.3 V ± 0.3 V						
A→Y Level Translation		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 50 pF, see Figure 37				
Propagation Delay	t <sub>P, A→Y</sub>		7	10	ns	
Rise Time	t <sub>R, A→Y</sub>		2.5	4	ns	
Fall Time	t <sub>F, A→Y</sub>		2	5	ns	
Maximum Data Rate	D <sub>MAX, A→Y</sub>		60		Mbps	
Channel-to-Channel Skew	t <sub>SKEW, A→Y</sub>		1.5	2	ns	
Part-to-Part Skew		t <sub>PPSKEW, A→Y</sub>		4	ns	
Y→A Level Translation						
Propagation Delay		R <sub>S</sub> = R <sub>T</sub> = 50 Ω, C <sub>L</sub> = 15 pF, see Figure 38				
Propagation Delay	t <sub>P, Y→A</sub>		5	8	ns	
Rise Time	t <sub>R, Y→A</sub>		1	4	ns	
Fall Time	t <sub>F, Y→A</sub>		3	5	ns	
Maximum Data Rate	D <sub>MAX, Y→A</sub>		60		Mbps	
Channel-to-Channel Skew	t <sub>SKEW, Y→A</sub>		2	3	ns	
Part-to-Part Skew		t <sub>PPSKEW, Y→A</sub>		3	ns	
<b>POWER REQUIREMENTS</b>						
Power Supply Voltages		V <sub>CCA</sub>	V <sub>CCA</sub> ≤ V <sub>CCY</sub>	1.15	5.5	V
		V <sub>CCY</sub>		1.65	5.5	V
Quiescent Power Supply Current		I <sub>CCA</sub>	V <sub>A</sub> = 0 V or V <sub>CCA</sub> , V <sub>Y</sub> = 0 V or V <sub>CCY</sub> , V <sub>CCA</sub> = V <sub>CCY</sub> = 5.5 V, EN = V <sub>CCY</sub>	0.17	1	μA
		I <sub>CCY</sub>	V <sub>A</sub> = 0 V or V <sub>CCA</sub> , V <sub>Y</sub> = 0 V or V <sub>CCY</sub> , V <sub>CCA</sub> = V <sub>CCY</sub> = 5.5 V, EN = V <sub>CCY</sub>	0.27	1	μA
Three-State Mode Power Supply Current		I <sub>HIGHZA</sub>	V <sub>CCA</sub> = V <sub>CCY</sub> = 5.5 V, EN = 0	0.1	1	μA
		I <sub>HIGHZY</sub>	V <sub>CCA</sub> = V <sub>CCY</sub> = 5.5 V, EN = 0	0.1	1	μA

<sup>1</sup> Temperature range is -40°C to +85°C (B Version) for the TSSOP, the LFCSP, the WLCSP, and the backside-coated WLCSP.

<sup>2</sup> All typical values are at T<sub>A</sub> = 25°C, unless otherwise noted.

<sup>3</sup> Guaranteed by design; not subject to production test.

## ABSOLUTE MAXIMUM RATINGS

T<sub>A</sub> = 25°C, unless otherwise noted.

Table 2.

Parameter	Rating
V <sub>CCA</sub> to GND	-0.3 V to +7 V
V <sub>CCY</sub> to GND	V <sub>CCA</sub> to +7 V
Digital Inputs (A)	-0.3 V to (V <sub>CCA</sub> + 0.3 V)
Digital Inputs (Y)	-0.3 V to (V <sub>CCY</sub> + 0.3 V)
EN to GND	-0.3 V to +7 V
Operating Temperature Range	
Extended Industrial Range (B Version)	-40°C to +85°C
Storage Temperature Range	-65°C to +150°C
Junction Temperature	150°C
θ <sub>JA</sub> Thermal Impedance	
20-Lead TSSOP	78°C/W
20-Lead LFCSP	30.4°C/W
20-Ball WLCSP	100°C/W
Lead Temperature, Soldering (10 sec)	300°C
IR Reflow, Peak Temperature (<20 sec)	260°C (+0°C/-5°C)

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

Only one absolute maximum rating may be applied at any one time.

### ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

# PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

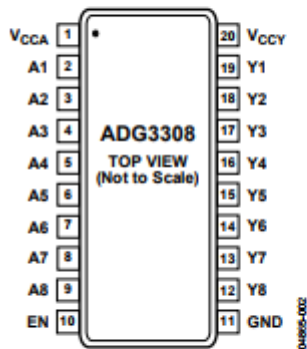
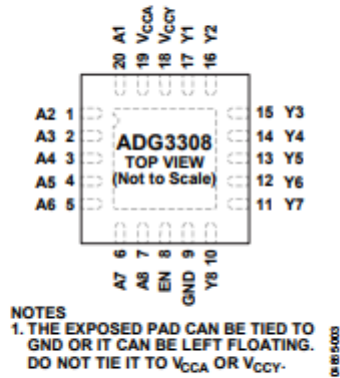


Figure 2. 20-Lead TSSOP



NOTES  
1. THE EXPOSED PAD CAN BE TIED TO GND OR IT CAN BE LEFT FLOATING. DO NOT TIE IT TO V<sub>CCA</sub> OR V<sub>CCY</sub>.

Figure 3. 20-Lead LFCSP

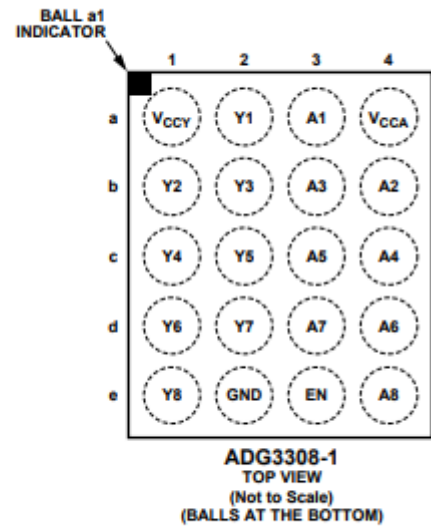


Figure 4. 20-Ball WLCSP

Table 3. Pin Function Descriptions

Pin/Ball No.			Mnemonic	Description
TSSOP	LFCSP	WLCSP		
1	19	a4	V <sub>CCA</sub>	Power Supply. Power supply voltage input for the A1 I/O pin to the A8 I/O pin ( $1.15\text{ V} \leq V_{CCA} < V_{CCY}$ ).
2	20	a3	A1	Input/Output A1. Referenced to V <sub>CCA</sub> .
3	1	b4	A2	Input/Output A2. Referenced to V <sub>CCA</sub> .
4	2	b3	A3	Input/Output A3. Referenced to V <sub>CCA</sub> .
5	3	c4	A4	Input/Output A4. Referenced to V <sub>CCA</sub> .
6	4	c3	A5	Input/Output A5. Referenced to V <sub>CCA</sub> .
7	5	d4	A6	Input/Output A6. Referenced to V <sub>CCA</sub> .
8	6	d3	A7	Input/Output A7. Referenced to V <sub>CCA</sub> .
9	7	e4	A8	Input/Output A8. Referenced to V <sub>CCA</sub> .
10	8	e3	EN	Active High Enable Input.
11	9	e2	GND	Ground.
12	10	e1	Y8	Input/Output Y8. Referenced to V <sub>CCY</sub> .
13	11	d2	Y7	Input/Output Y7. Referenced to V <sub>CCY</sub> .
14	12	d1	Y6	Input/Output Y6. Referenced to V <sub>CCY</sub> .
15	13	c2	Y5	Input/Output Y5. Referenced to V <sub>CCY</sub> .
16	14	c1	Y4	Input/Output Y4. Referenced to V <sub>CCY</sub> .
17	15	b2	Y3	Input/Output Y3. Referenced to V <sub>CCY</sub> .
18	16	b1	Y2	Input/Output Y2. Referenced to V <sub>CCY</sub> .
19	17	a2	Y1	Input/Output Y1. Referenced to V <sub>CCY</sub> .
20	18	a1	V <sub>CCY</sub>	Power Supply. Power supply voltage input for the Y1 I/O pin to the Y8 I/O pin ( $1.65\text{ V} \leq V_{CCY} \leq 5.5\text{ V}$ ).

# TYPICAL PERFORMANCE CHARACTERISTICS

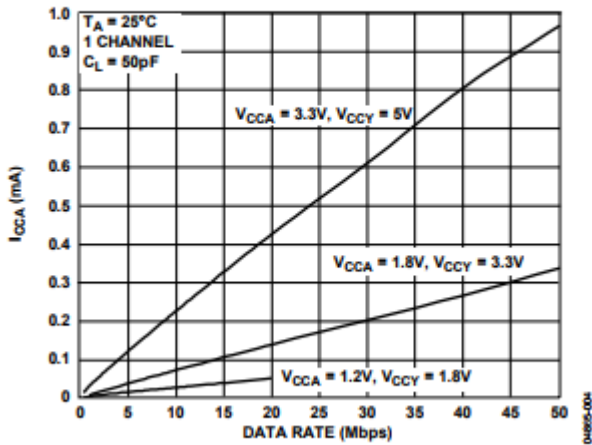


Figure 5.  $I_{CCA}$  vs. Data Rate (A→Y Level Translation)

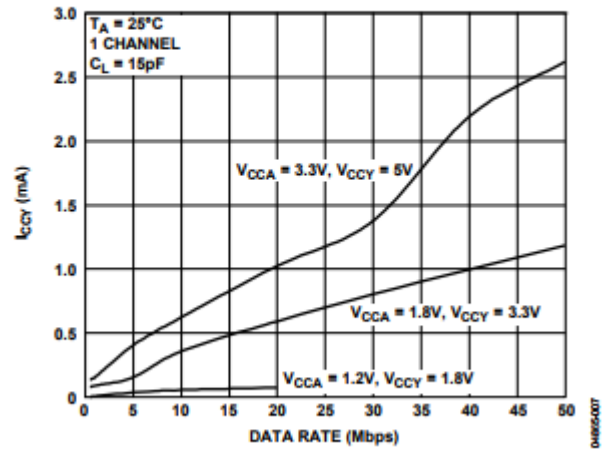


Figure 8.  $I_{CCY}$  vs. Data Rate (Y→A Level Translation)

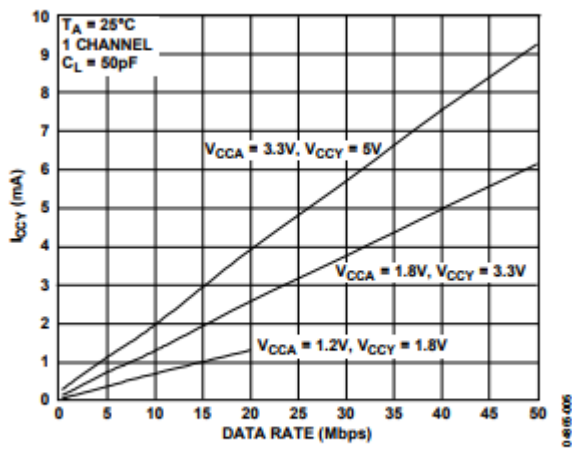


Figure 6.  $I_{CCY}$  vs. Data Rate (A→Y Level Translation)

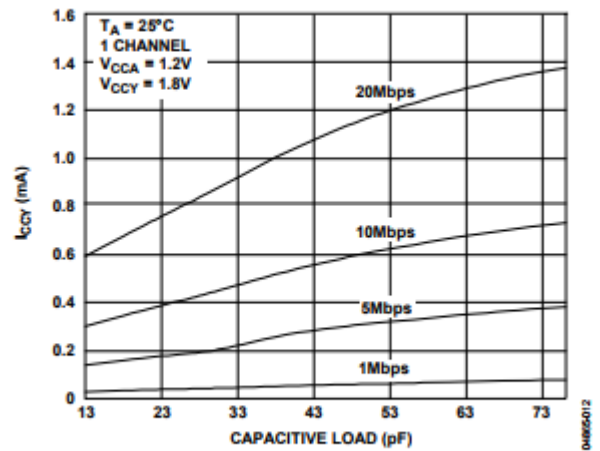


Figure 9.  $I_{CCY}$  vs. Capacitive Load at Pin Y for A→Y (1.2 V→1.8 V) Level Translation

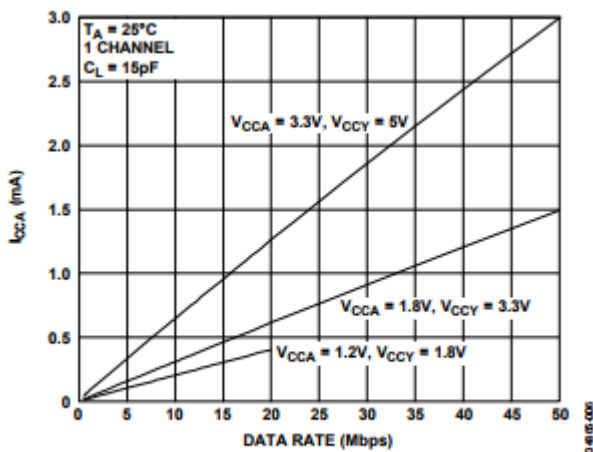


Figure 7.  $I_{CCA}$  vs. Data Rate (Y→A Level Translation)

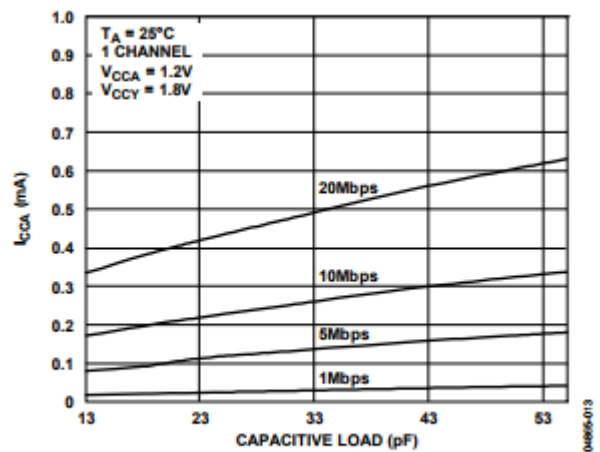


Figure 10.  $I_{CCA}$  vs. Capacitive Load at Pin A for Y→A (1.8 V→1.2 V) Level Translation

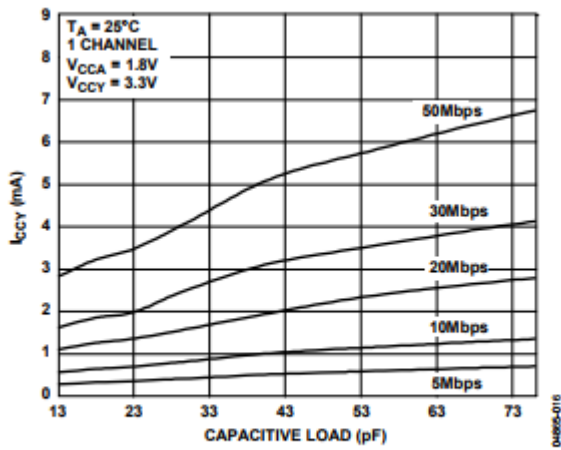


Figure 11.  $I_{CCY}$  vs. Capacitive Load at Pin Y for A→Y (1.8 V→3.3 V) Level Translation

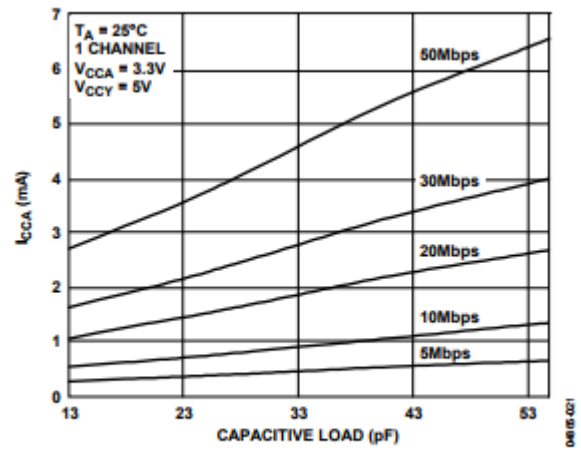


Figure 14.  $I_{CCA}$  vs. Capacitive Load at Pin A for Y→A (5 V→3.3 V) Level Translation

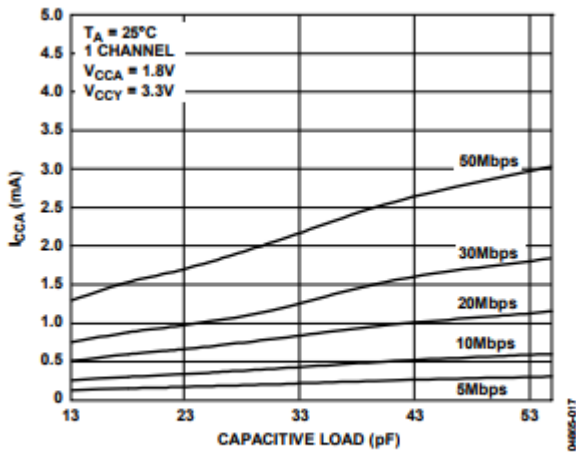


Figure 12.  $I_{CCA}$  vs. Capacitive Load at Pin A for Y→A (3.3 V→1.8 V) Level Translation

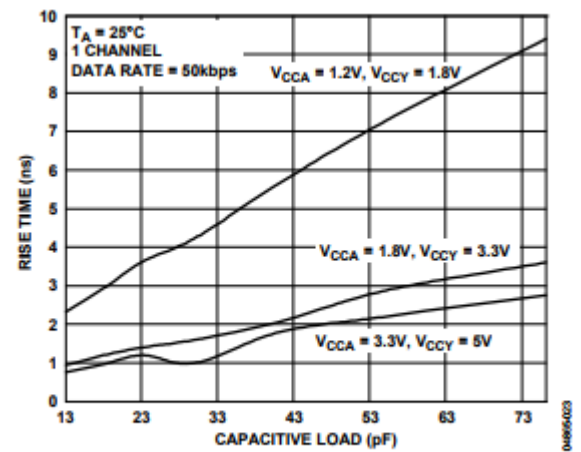


Figure 15. Rise Time vs. Capacitive Load at Pin Y (A→Y Level Translation)

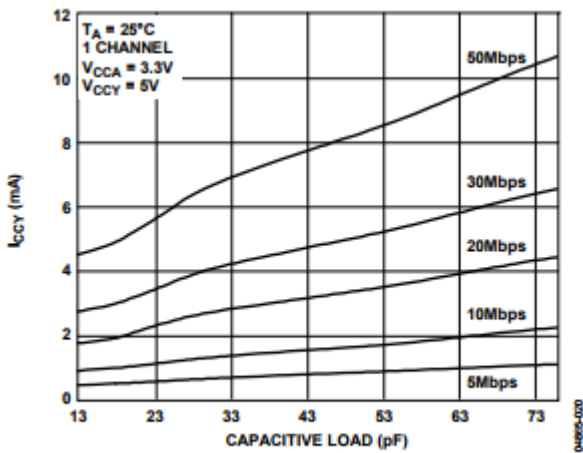


Figure 13.  $I_{CCY}$  vs. Capacitive Load at Pin Y for A→Y (3.3 V→5 V) Level Translation

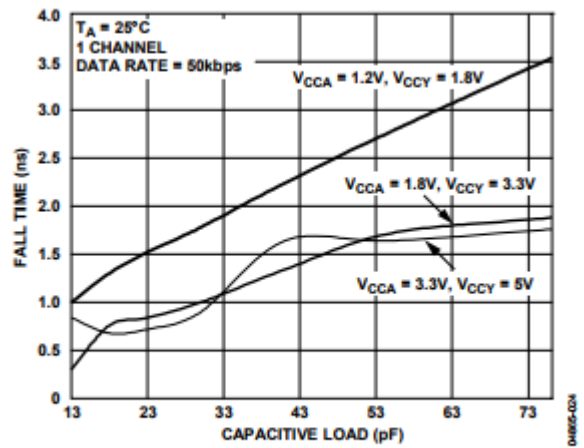


Figure 16. Fall Time vs. Capacitive Load at Pin Y (A→Y Level Translation)

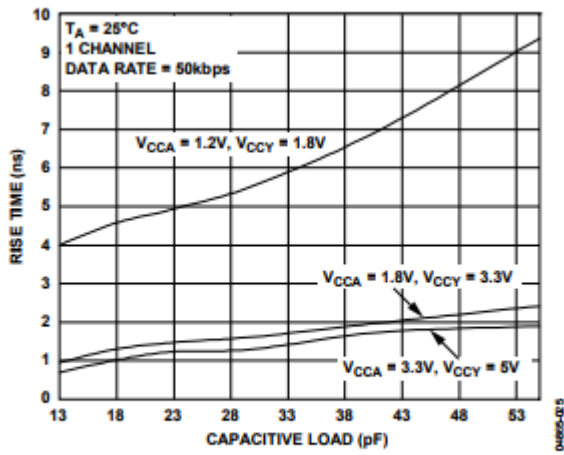


Figure 17. Rise Time vs. Capacitive Load at Pin A (Y→A Level Translation)

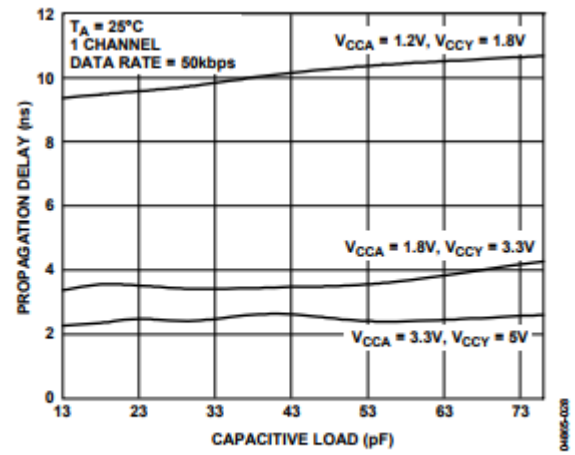


Figure 20. Propagation Delay ( $t_{PH}$ ) vs. Capacitive Load at Pin Y (A→Y Level Translation)

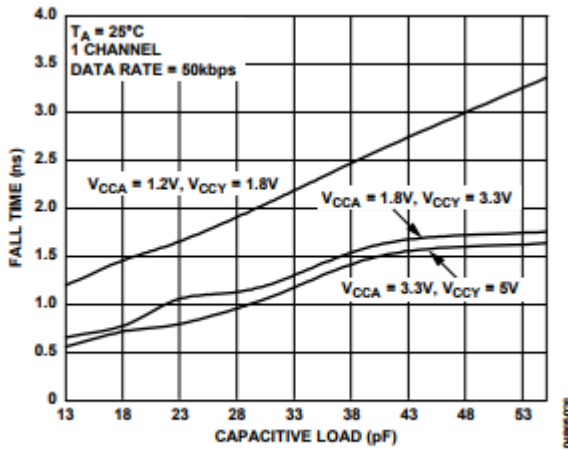


Figure 18. Fall Time vs. Capacitive Load at Pin A (Y→A Level Translation)

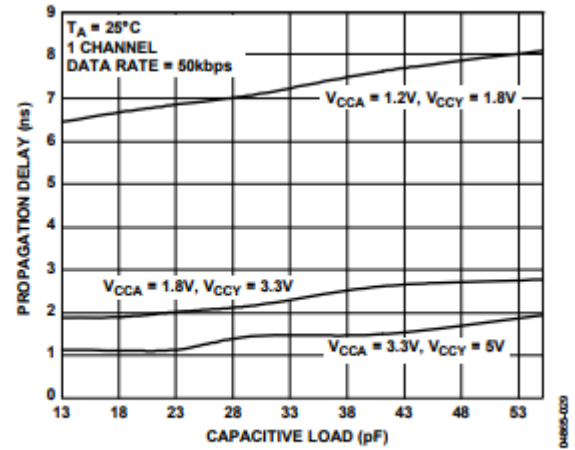


Figure 21. Propagation Delay ( $t_{PLH}$ ) vs. Capacitive Load at Pin A (Y→A Level Translation)

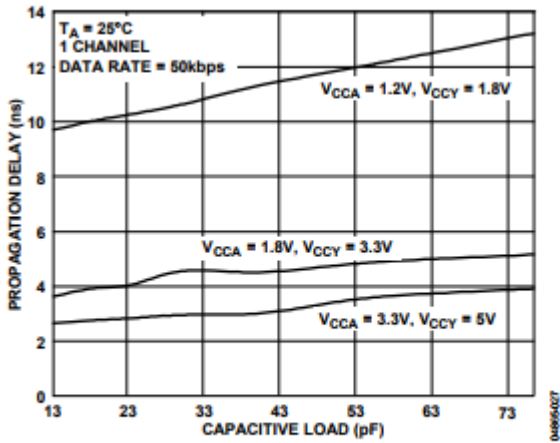


Figure 19. Propagation Delay ( $t_{PLH}$ ) vs. Capacitive Load at Pin Y (A→Y Level Translation)

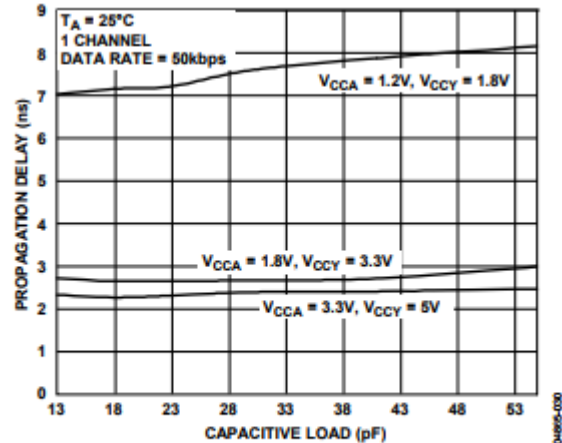


Figure 22. Propagation Delay ( $t_{PLH}$ ) vs. Capacitive Load at Pin A (Y→A Level Translation)



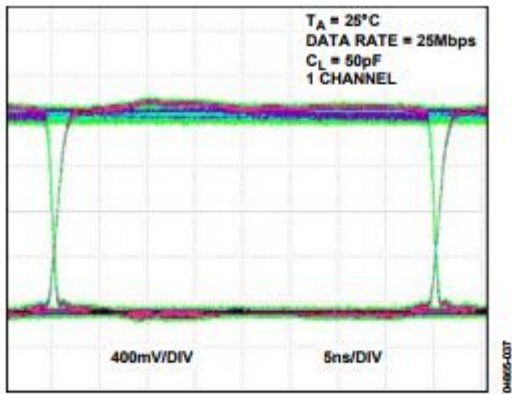


Figure 23. Eye Diagram at Y Output  
(1.2 V→1.8 V Level Transition, 25 Mbps)

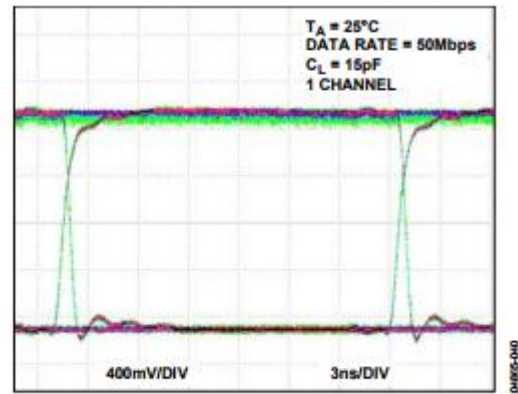


Figure 26. Eye Diagram at A Output  
(3.3 V→1.8 V Level Transition, 50 Mbps)

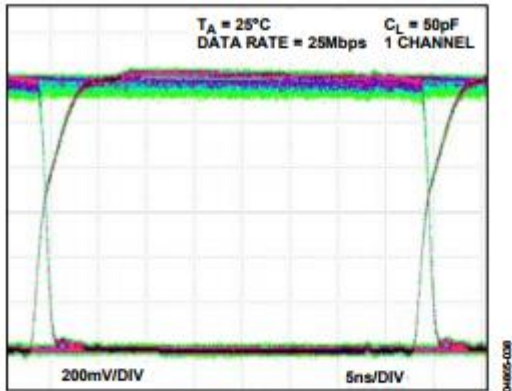


Figure 24. Eye Diagram at A Output  
(1.8 V→1.2 V Level Transition, 25 Mbps)

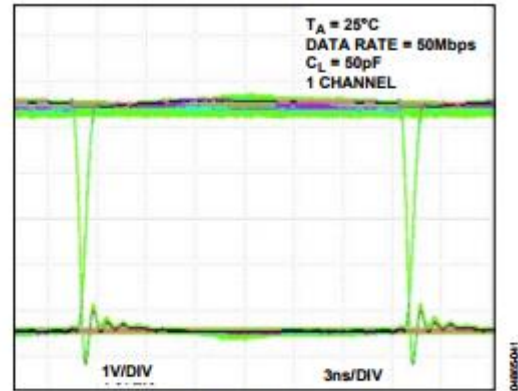


Figure 27. Eye Diagram at Y Output  
(3.3 V→5 V Level Transition, 50 Mbps)

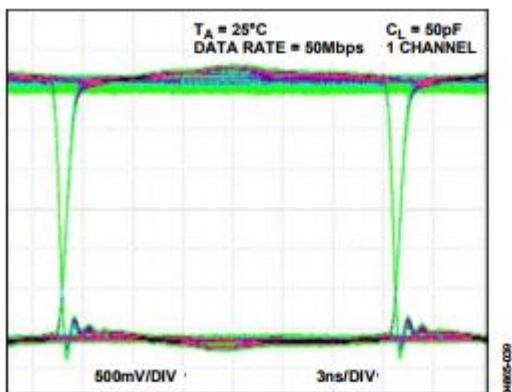


Figure 25. Eye Diagram at Y Output  
(1.8 V→3.3 V Level Transition, 50 Mbps)

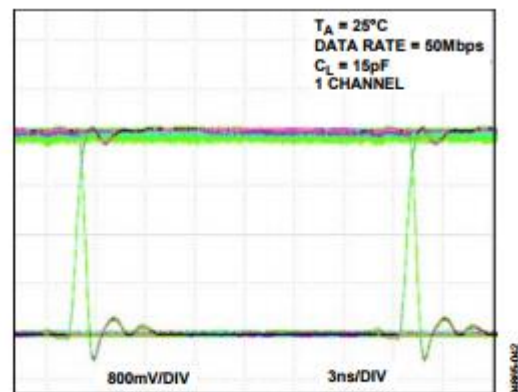


Figure 28. Eye Diagram at A Output  
(5 V→3.3 V Level Transition, 50 Mbps)

# TEST CIRCUITS

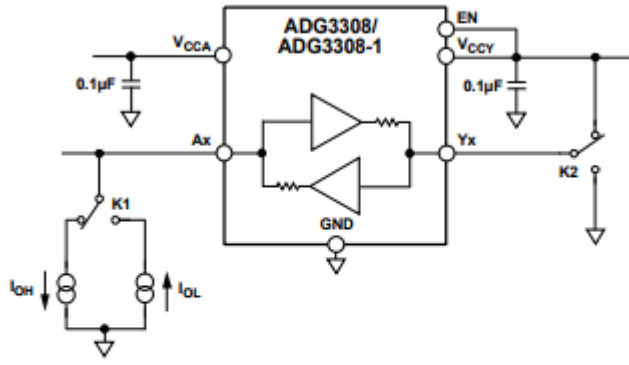


Figure 29.  $V_{OH}/V_{OA}$  Voltages at Pin A

01855-013

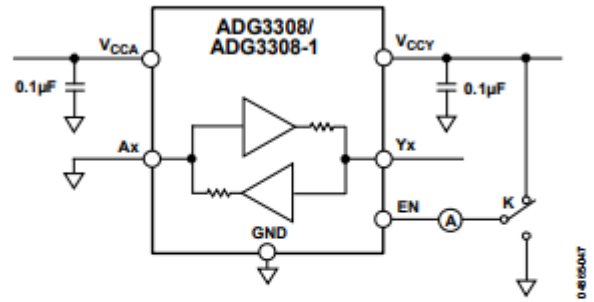


Figure 33. EN Pin Leakage Current

01855-017

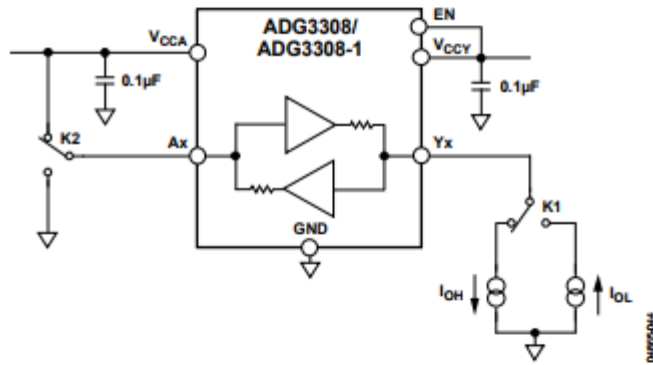


Figure 30.  $V_{OH}/V_{OA}$  Voltages at Pin Y

01855-014

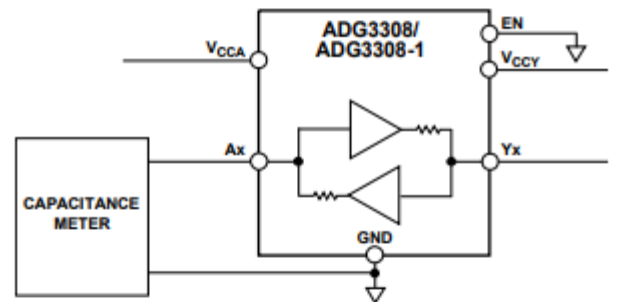


Figure 34. Capacitance at Pin A

01855-015

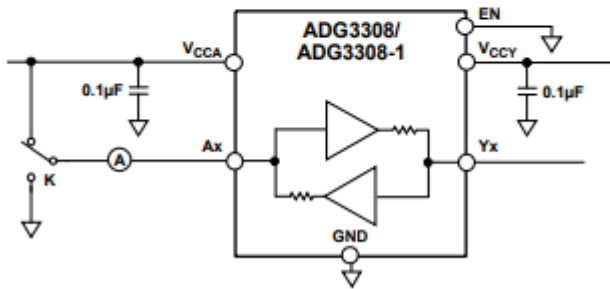


Figure 31. Three-State Leakage Current at Pin A

01855-016

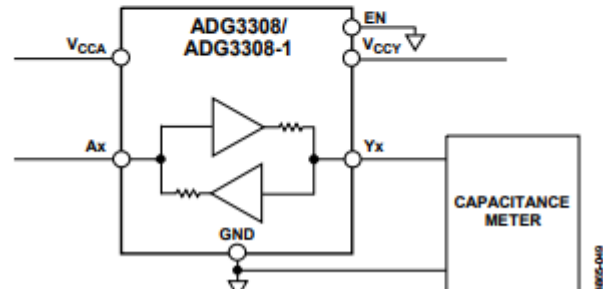


Figure 35. Capacitance at Pin Y

01855-018

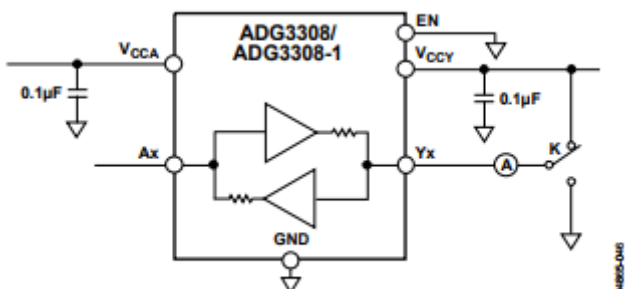
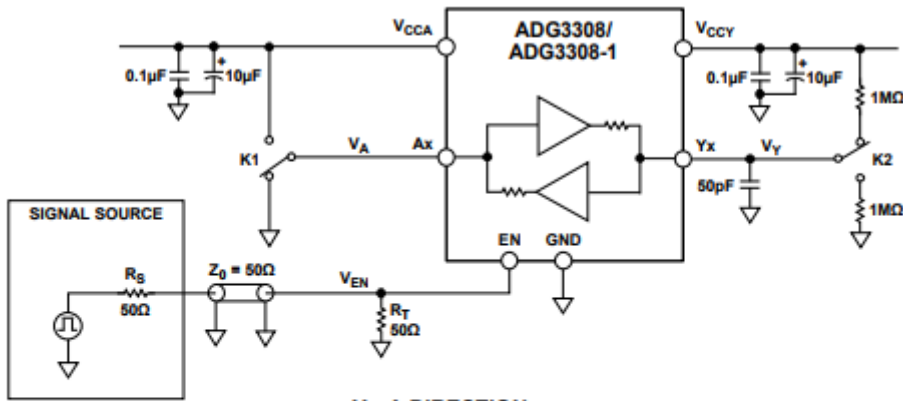


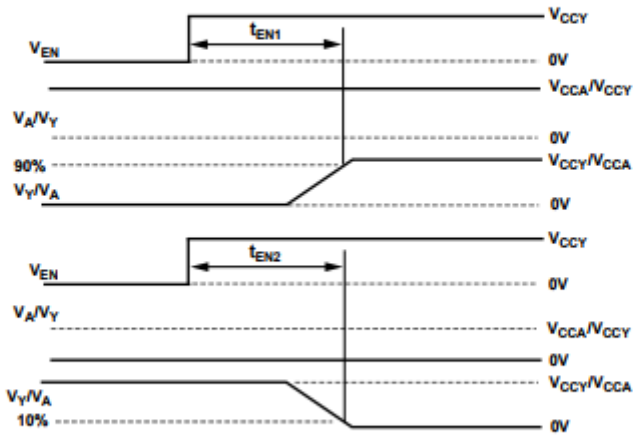
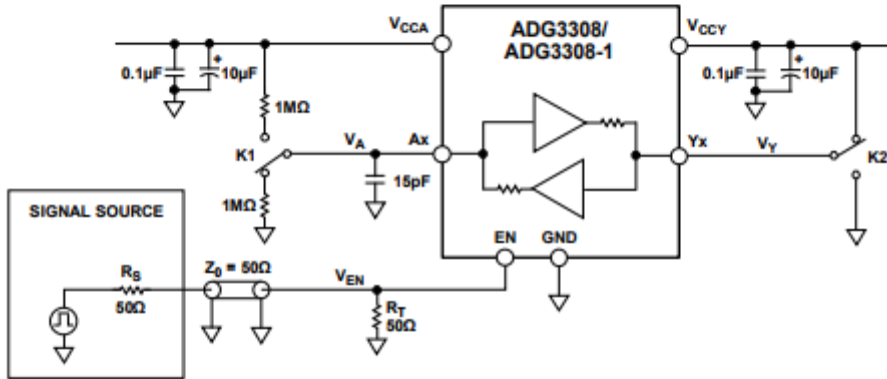
Figure 32. Three-State Leakage Current at Pin Y

01855-019

**A→Y DIRECTION**



**Y→A DIRECTION**



**NOTES**

1.  $t_{EN}$  IS WHICHEVER IS LARGER BETWEEN  $t_{EN1}$  AND  $t_{EN2}$  IN BOTH A→Y AND Y→A DIRECTIONS.

Figure 36. Enable Time

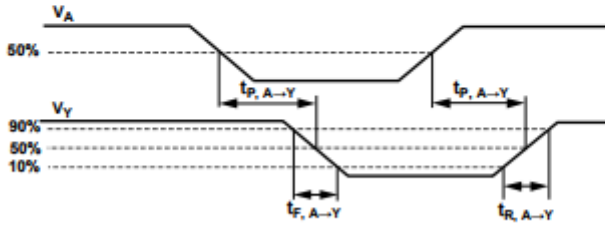
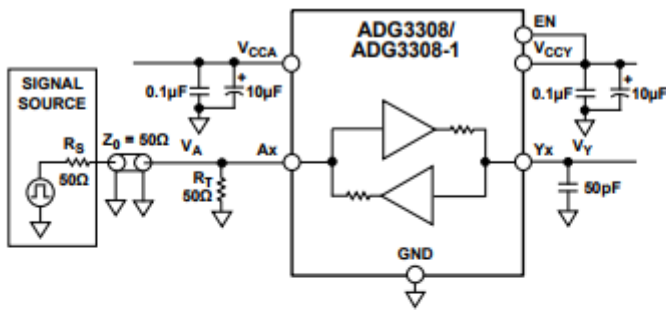


Figure 37. Switching Characteristics (A→Y Level Translation)

04869-001

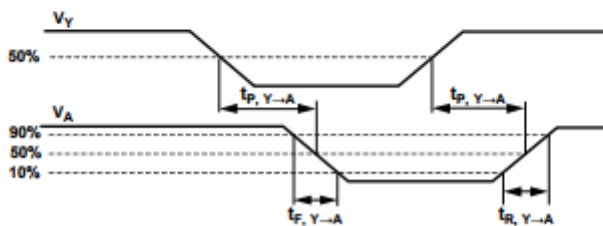
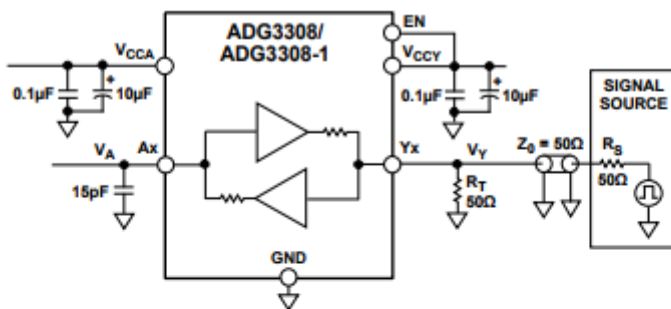


Figure 38. Switching Characteristics (Y→A Level Translation)

04869-002

## TERMINOLOGY

$V_{IH A}$

Logic input high voltage at Pin A1 to Pin A8.

$V_{IL A}$

Logic input low voltage at Pin A1 to Pin A8.

$V_{OHA}$

Logic output high voltage at Pin A1 to Pin A8.

$V_{OLA}$

Logic output low voltage at Pin A1 to Pin A8.

$C_A$

Capacitance measured at Pin A1 to Pin A8 (EN = 0).

$I_{LA, HIGH-Z}$

Leakage current at Pin A1 to Pin A8 when EN = 0 (high impedance state at Pin A1 to Pin A8).

$V_{IH Y}$

Logic input high voltage at Pin Y1 to Pin Y8.

$V_{IL Y}$

Logic input low voltage at Pin Y1 to Pin Y8.

$V_{OH Y}$

Logic output high voltage at Pin Y1 to Pin Y8.

$V_{OL Y}$

Logic output low voltage at Pin Y1 to Pin Y8.

$D_{MAX, A \rightarrow Y}$

Guaranteed data rate when translating logic levels in the A→Y direction under the driving and loading conditions specified in Table 1.

$t_{SKEW, A \rightarrow Y}$

Difference between propagation delays on any two channels when translating logic levels in the A→Y direction.

$t_{PPSKEW, A \rightarrow Y}$

Difference in propagation delay between any one channel and the same channel on a different part (under same driving/loading conditions) when translating in the A→Y direction.

$t_{P, Y \rightarrow A}$

Propagation delay when translating logic levels in the Y→A direction.

$t_{R, Y \rightarrow A}$

Rise time when translating logic levels in the Y→A direction.

$t_{F, Y \rightarrow A}$

Fall time when translating logic levels in the Y→A direction.

$D_{MAX, Y \rightarrow A}$

Guaranteed data rate when translating logic levels in the Y→A direction under the driving and loading conditions specified in Table 1.

$C_Y$

Capacitance measured at Pin Y1 to Pin Y8 ( $EN = 0$ ).

$I_{L, HIGH-Z}$

Leakage current at Pin Y1 to Pin Y8 when  $EN = 0$  (high impedance state at Pin Y1 to Pin Y8).

$V_{IHEN}$

Logic input high voltage at the EN pin.

$V_{ILEN}$

Logic input low voltage at the EN pin.

$C_{EN}$

Capacitance measured at EN pin.

$I_{LEN}$

Enable (EN) pin leakage current.

$t_{EN}$

Three-state enable time for Pin A1 to Pin A8/Pin Y1 to Pin Y8.

$t_{P, A \rightarrow Y}$

Propagation delay when translating logic levels in the  $A \rightarrow Y$  direction.

$t_{R, A \rightarrow Y}$

Rise time when translating logic levels in the  $A \rightarrow Y$  direction.

$t_{F, A \rightarrow Y}$

Fall time when translating logic levels in the  $A \rightarrow Y$  direction.

## THEORY OF OPERATION

The **ADG3308/ADG3308-1** level translators allow the level shifting necessary for data transfer in a system where multiple supply voltages are used. The device requires two supplies,  $V_{CCA}$  and  $V_{CCY}$  ( $V_{CCA} \leq V_{CCY}$ ). These supplies set the logic levels on each side of the device. When driving the A pins, the device translates the  $V_{CCA}$  compatible logic levels to  $V_{CCY}$  compatible logic levels available at the Y pins. Similarly, because the device is capable of bidirectional translation, when driving the Y pins the  $V_{CCY}$  compatible logic levels are translated to the  $V_{CCA}$  compatible logic levels available at the A pins. When  $EN = 0$ , the A1 pin to the A8 pin and the Y1 pin to the Y8 pin are three-stated. When EN is driven high, the **ADG3308/ADG3308-1** go into normal operation mode and perform level translation.

### LEVEL TRANSLATOR ARCHITECTURE

The **ADG3308/ADG3308-1** consist of eight bidirectional channels. Each channel can translate logic levels in either the  $A \rightarrow Y$  or the  $Y \rightarrow A$  direction. They use a one-shot accelerator architecture, ensuring excellent switching characteristics.

Figure 39 shows a simplified block diagram of a bidirectional channel.

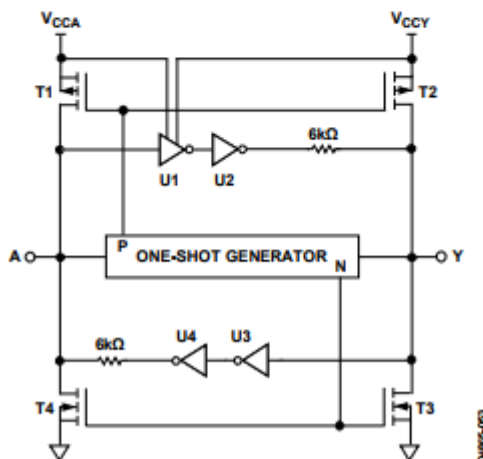


Figure 39. Simplified Block Diagram of an **ADG3308/ADG3308-1** Channel

$t_{SKEW, Y \rightarrow A}$

Difference between propagation delays on any two channels when translating logic levels in the  $Y \rightarrow A$  direction.

$t_{PPSKEW, Y \rightarrow A}$

Difference in propagation delay between any one channel and the same channel on a different part (under same driving/loading conditions) when translating in the  $Y \rightarrow A$  direction.

$V_{CCA}$

$V_{CCA}$  supply voltage.

$V_{CCY}$

$V_{CCY}$  supply voltage.

$I_{CCA}$

$V_{CCA}$  supply current.

$I_{CCY}$

$V_{CCY}$  supply current.

$I_{HIGH-ZA}$

$V_{CCA}$  supply current during three-state mode ( $EN = 0$ ).

$I_{HIGH-ZY}$

$V_{CCY}$  supply current during three-state mode ( $EN = 0$ ).

### INPUT DRIVING REQUIREMENTS

To ensure correct operation of the **ADG3308/ADG3308-1**, the circuit that drives the input of the device should be able to ensure rise/fall times of less than 3 ns when driving a load consisting of a 6 k $\Omega$  resistor in parallel with the input capacitance of the **ADG3308/ADG3308-1** channel.

### OUTPUT LOAD REQUIREMENTS

The **ADG3308/ADG3308-1** level translators are designed to drive CMOS-compatible loads. If current-driving capability is required, it is recommended to use buffers between the **ADG3308/ADG3308-1** outputs and the load.

### ENABLE OPERATION

The **ADG3308/ADG3308-1** provide three-state operation at the A I/O pins and the Y I/O pins by using the enable (EN) pin, as shown in Table 4.

Table 4. Truth Table

EN	Y I/O Pins	A I/O Pins
0	High-Z <sup>1</sup>	High-Z <sup>1</sup>
1	Normal operation <sup>2</sup>	Normal operation <sup>2</sup>

<sup>1</sup> High impedance state.

<sup>2</sup> In normal operation, the **ADG3308/ADG3308-1** perform level translation.

When  $EN = 0$ , the **ADG3308/ADG3308-1** enter into three-state mode. In this mode, the current consumption from both the  $V_{CCA}$  and  $V_{CCY}$  supplies is reduced, allowing the user to save power, which is critical, especially in battery-operated systems. The EN input pin can only be driven with  $V_{CCY}$  compatible logic levels for the **ADG3308**, whereas the **ADG3308-1** can be driven with either  $V_{CCA}$  or  $V_{CCY}$  compatible logic levels.

### POWER SUPPLIES

For proper operation of the device, the voltage applied to the  $V_{CCA}$  must always be less than or equal to the voltage applied to  $V_{CCY}$ . To meet this condition, the recommended power-up sequence is  $V_{CCY}$  first and then  $V_{CCA}$ . The **ADG3308/ADG3308-1** operate properly only after both supply voltages reach their

The logic level translation in the A→Y direction is performed using a level translator (U1) and an inverter (U2), whereas the translation in the Y→A direction is performed using the U3 inverter and U4 inverter. The one-shot generator detects a rising or falling edge present on either the A side or the Y side of the channel. It sends a short pulse that turns on the PMOS transistors (T1 and T2) for a rising edge, or the NMOS transistors (T3 and T4) for a falling edge. This charges/discharges the capacitive load faster, resulting in fast rise and fall times.

The inputs of the unused channels (A or Y) should be tied to their corresponding V<sub>CC</sub> rail (V<sub>CCA</sub> or V<sub>CCY</sub>) or to GND.

## DATA RATE

The maximum data rate at which the device is guaranteed to operate is a function of the V<sub>CCA</sub> and V<sub>CCY</sub> supply voltage combination and the load capacitance. It represents the maximum frequency of a square wave that can be applied to the I/O pins, ensuring that the device operates within the data sheet specifications in terms of output voltage (V<sub>OL</sub> and V<sub>OH</sub>) and power dissipation (the junction temperature does not exceed the value specified under the Absolute Maximum Ratings section). Table 5 shows the guaranteed data rates at which the ADG3308/ADG3308-1 can operate in both directions (A→Y level translation or Y→A level translation) for various V<sub>CCA</sub> and V<sub>CCY</sub> supply combinations.

Table 5. Guaranteed Data Rates<sup>1</sup>

V <sub>CCA</sub>	V <sub>CCY</sub>			
	1.8 V (1.65 V to 1.95 V)	2.5 V (2.3 V to 2.7 V)	3.3 V (3.0 V to 3.6 V)	5 V (4.5 V to 5.5 V)
1.2 V (1.15 V to 1.3 V)	25 Mbps	30 Mbps	40 Mbps	40 Mbps
1.8 V (1.65 V to 1.95 V)		45 Mbps	50 Mbps	50 Mbps
2.5 V (2.3 V to 2.7 V)			60 Mbps	50 Mbps
3.3 V (3.0 V to 3.6 V)				50 Mbps
5 V (4.5 V to 5.5 V)				

<sup>1</sup> The load capacitance used is 50 pF when translating in the A→Y direction and 15 pF when translating in the Y→A direction.

nominal values. It is not recommended to use the part in a system where, during power-up, V<sub>CCA</sub> may be greater than V<sub>CCY</sub> due to a significant increase in the current taken from the V<sub>CCA</sub> supply. For optimum performance, the V<sub>CCA</sub> and V<sub>CCY</sub> pins should be decoupled to GND as close as possible to the device.

## APPLICATIONS

The ADG3308/ADG3308-1 are designed for digital circuits that operate at different supply voltages; therefore, logic level translation is required. The lower voltage logic signals are connected to the A pins, and the higher voltage logic signals to the Y pins. The ADG3308/ADG3308-1 can provide level translation in both directions (A→Y or Y→A) on all eight channels, eliminating the need for a level translator IC for each direction. The internal architecture allows the ADG3308/ADG3308-1 to perform bidirectional level translation without an additional signal to set the direction in which the translation is made. It also allows simultaneous data flow in both directions on the same part, for example, when two channels translate in the A→Y direction while the other two translate in the Y→A direction. This simplifies the design by eliminating the timing requirements for the direction signal and reduces the number of ICs used for level translation.

Figure 40 shows an application where a 3.3 V microprocessor can read or write data to and from a 1.8 V peripheral device using an 8-bit bus.

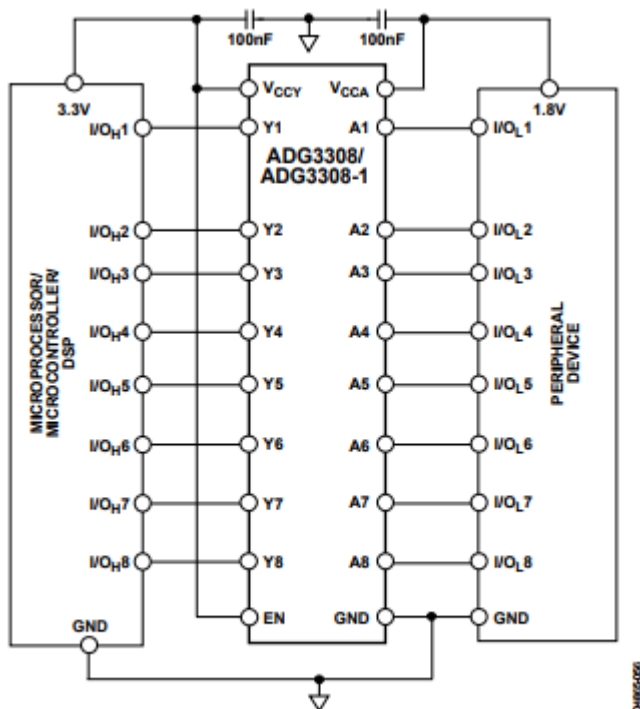


Figure 40. 1.8 V to 3.3 V 8-Bit Level Translation Circuit

When the application requires level translation between a microprocessor and multiple peripheral devices, the ADG3308/ADG3308-1 I/O pins can be three-stated by setting  $EN = 0$ . This feature allows the ADG3308/ADG3308-1 to share the data buses with other devices without causing contention issues. Figure 41 shows an application where a 3.3 V microprocessor is connected to 1.8 V peripheral devices using the three-state feature.

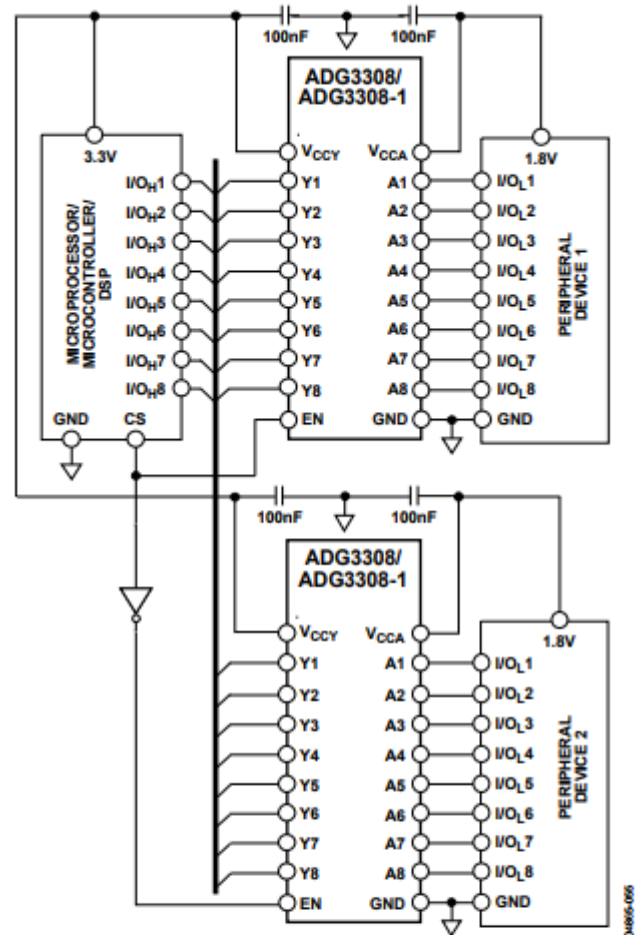


Figure 41. 1.8 V to 3.3 V Level Translation Circuit Using the Three-State Feature

## LAYOUT GUIDELINES

As with any high speed digital IC, the printed circuit board layout is important in the overall performance of the circuit. Care should be taken to ensure proper power supply bypass and return paths for the high speed signals. Each  $V_{CC}$  pin ( $V_{CCA}$  and  $V_{CCY}$ ) should be bypassed using low effective series resistance (ESR) and effective series inductance (ESI) capacitors placed as close as possible to the  $V_{CCA}$  and  $V_{CCY}$  pins. The parasitic inductance of the high speed signal track can cause significant overshoot. This effect can be reduced by keeping the length of the tracks as short as possible. A solid copper plane for the return path

(GND) is also recommended.